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T36-141808M/KOH

B1 6. (Amended) A semiconductor device according to claim 1, wherein said substrate comprises a cubic crystal material comprising a (111) face on which said undercoat layer is formed.

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8. (Amended) A method of forming a semiconductor device, comprising:  
forming an undercoat layer on a substrate, said undercoat layer comprising a metal nitride; and  
forming a group III nitride compound semiconductor layer on said undercoat layer, said group III nitride compound semiconductor layer being separated from said substrate by at least said undercoat layer.

9. (Amended) A method according to claim 8, further comprising:  
forming a buffer layer of a group III nitride compound semiconductor between said group III nitride compound semiconductor layer and said undercoat layer.

B2 10. (Amended) A method according to claim 9, wherein said forming said buffer layer comprises forming said buffer layer by a metal organic chemical vapor deposition method at a temperature substantially equal to or higher than the temperature for the growth of said group III nitride compound semiconductor layer.

11. (Amended) A method according to claim 9, wherein said forming said buffer layer comprises forming said buffer layer by any one of a sputtering method, an evaporation method and an ion plating method.

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B3 20. (Amended) A semiconductor device according to claim 1, further comprising:  
a first electrode provided on said undercoat layer.

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**Please add the following new claims:**

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B4 - - 23. A semiconductor device according to claim 1, wherein said undercoat layer is selected for providing a predetermined crystallinity of said group III nitride compound semiconductor

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layer.

24. A semiconductor device according to claim 1, wherein said metal nitride comprises at least one of Nb, V, Y, and Cr.

25. A semiconductor device according to claim 1, wherein said undercoat layer has a thickness in a range of 0.1 to 10  $\mu\text{m}$ .

26. A semiconductor device according to claim 1, further comprising:  
a metal layer adjacent to said undercoat layer.

27. A semiconductor device according to claim 1, wherein said group III nitride compound semiconductor layer comprises a light-emitting layer.

28. A semiconductor device according to claim 27, wherein said undercoat layer reflects light emitted from said light-emitting layer.

29. A semiconductor device according to claim 1, wherein said undercoat layer comprises a continuously-formed undercoat layer.

30. A method of forming a semiconductor device according to claim 8, further comprising:

heating said undercoat layer at a temperature of from 600 to 1200°C before said forming said group III nitride compound semiconductor layer.

31. A method according to claim 30, wherein said forming said undercoat layer comprises forming said undercoat layer by one of chemical vapor deposition and physical vapor deposition. - -

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